

Abstract of the Disclosure

The present invention provides a semiconductor memory device and a fabrication method capable of preventing the
5 contact between a dielectric layer of a capacitor and a diffusion barrier. The plug comprises a diffusion barrier layer and a seed layer for forming a lower electrode of a capacitor. Accordingly, it is possible to prevent the dielectric layer being contacted with the diffusion barrier,
10 whereby the leakage current may be reduced, and the capacitance of the capacitor may be increased.

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